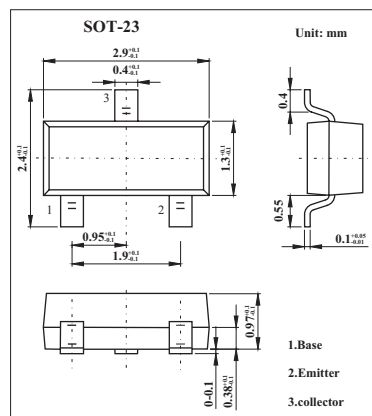


## 2SB1295

### ■ Features

- Large current capacity.
- Low collector to emitter saturation voltage.
- Very small-sized package permitting sets to be made smaller and slimer.



### ■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V <sub>CB0</sub>	-15	V
Collector-emitter voltage	V <sub>CEO</sub>	-15	V
Emitter-base voltage	V <sub>EBO</sub>	-5	V
Collector current	I <sub>C</sub>	-0.8	A
Collector current (pulse)	I <sub>CP</sub>	-3	A
Collector dissipation	P <sub>C</sub>	200	mW
Jumction temperature	T <sub>j</sub>	150	°C
Storage temperature	T <sub>stg</sub>	-55 to +150	°C

### ■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector cutoff current	I <sub>CBO</sub>	V <sub>CB</sub> = -12V , I <sub>E</sub> = 0			-100	nA
Emitter cutoff current	I <sub>EBO</sub>	V <sub>EB</sub> = -4V , I <sub>C</sub> = 0			-100	nA
DC current Gain	h <sub>FE</sub>	V <sub>CE</sub> = -2V , I <sub>C</sub> = -50mA	135		600	
Gain bandwidth product	f <sub>T</sub>	V <sub>CE</sub> = -2V , I <sub>C</sub> = -50mA		300		MHz
Output capacitance	C <sub>ob</sub>	V <sub>CB</sub> = -10V , f = 1MHz		15		pF
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> = -5mA , I <sub>B</sub> = -0.5mA		-10	-25	mV
	V <sub>CE(sat)</sub>	I <sub>C</sub> = -400mA , I <sub>B</sub> = -20mA		-100	-200	mV
Base-to-emitter saturation voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> = -400mA , I <sub>B</sub> = -20mA		-0.9	-1.2	V
Collector-to-base breakdown voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> = -10μA , I <sub>E</sub> = 0	-15			V
Collector-to-emitter breakdown voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> = -1mA , R <sub>BE</sub> = ∞	-15			V
Emitter-to-base breakdown voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> = -10μA , I <sub>C</sub> = 0	-5			V

### ■ hFE Classification

Marking	UL		
Rank	5	6	7
hFE	135~270	200~400	300~600